BS107, BS107A

Preferred Device

Small Signal MOSFET 250 mAmps, 200 Volts

N-Channel TO-92

Features

- AEC Qualified
- PPAP Capable
- Pb-Free Package is Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	200	Vdc
Gate-Source Voltage - Continuous - Non-repetitive (t _p ≤ 50 μs)	V _{GS} V _{GSM}	±20 ±30	Vdc Vpk
Drain Current Continuous (Note 1) Pulsed (Note 2)	I _D	250 500	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	350	mW
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to 150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- The Power Dissipation of the package may result in a lower continuous drain current
- 2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

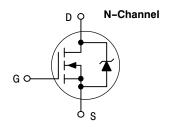


ON Semiconductor®

250 mAMPS, 200 VOLTS

 $R_{DS(on)} = 14 \Omega \text{ (BS107)}$

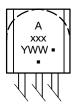
 $R_{DS(on)} = 6.4 \Omega \text{ (BS107A)}$



MARKING DIAGRAM



TO-92 CASE 29-11 STYLE 30



xxx = BS107 or BS107A A = Assembly Location

Y = Year

WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping
BS107	TO-92	1000 Units/Box
BS107G	TO-92 (Pb-Free)	1000 Units/Box
BS107A	TO-92	1000 Units/Box
BS107AG	TO-92 (Pb-Free)	1000 Units/Box
BS107ARL1	TO-92	2000/Ammo Pack
BS107ARL1G	TO-92 (Pb-Free)	2000/Ammo Pack

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Preferred devices are recommended choices for future use and best overall value.

BS107, BS107A

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Zero-Gate-Voltage Drain Current (V _{DS} = 130 Vdc, V _{GS} = 0)	I _{DSS}	-	-	30	nAdc
Drain-Source Breakdown Voltage (V _{GS} = 0, I _D = 100 μAdc)	V _{(BR)DSX}	200	-	-	Vdc
Gate Reverse Current (V _{GS} = 15 Vdc, V _{DS} = 0)	I _{GSS}	1	0.01	10	nAdc
ON CHARACTERISTICS (Note 3)					
Gate Threshold Voltage (I _D = 1.0 mAdc, V _{DS} = V _{GS})	V _{GS(Th)}	1.0	-	3.0	Vdc
Static Drain–Source On Resistance BS107 ($V_{GS} = 2.6 \text{ Vdc}$, $I_D = 20 \text{ mAdc}$) ($V_{GS} = 10 \text{ Vdc}$, $I_D = 200 \text{ mAdc}$) BS107A ($V_{GS} = 10 \text{ Vdc}$) ($I_D = 100 \text{ mAdc}$) ($I_D = 250 \text{ mAdc}$)	r _{DS(on)}		- - 4.5 4.8	28 14 6.0 6.4	Ω
SMALL-SIGNAL CHARACTERISTICS					1
Input Capacitance $(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz})$	C _{iss}	-	60	-	pF
Reverse Transfer Capacitance (V _{DS} = 25 Vdc, V _{GS} = 0, f = 1.0 MHz)	C _{rss}	-	6.0	-	pF
Output Capacitance $(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz})$	C _{oss}	ı	30	-	pF
Forward Transconductance (V _{DS} = 25 Vdc, I _D = 250 mAdc)	9fs	200	400	-	mmhos
SWITCHING CHARACTERISTICS					
Turn-On Time	t _{on}	ı	6.0	15	ns
Turn-Off Time	t _{off}	-	12	15	ns

^{3.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

RESISTIVE SWITCHING

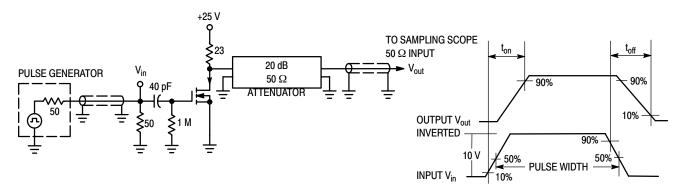


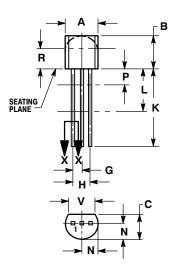
Figure 1. Switching Test Circuit

Figure 2. Switching Waveforms

BS107, BS107A

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**



STRAIGHT LEAD **BULK PACK**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	INCHES MILLIMETERS		
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	

STYLE 30: PIN 1. DRAIN

- 2. GATE 3. SOURCE